

Description

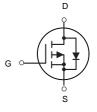
The HSTD20P3H6AG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

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TO-252-2L

General Features

 $V_{DS} = -30V I_D = -20A$ $R_{DS(ON)} < 42 \text{ m}\Omega @ V_{GS} = 10V$



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HSTD20P3H6AG	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Symbol	Parameter	Rating		
VDS	Drain-Source Voltage	-30	V	
VGS	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	-20	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	-15	А	
IDM	Pulsed Drain Current ²	-50	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	29	W	
TSTG	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
ReJA	Thermal Resistance Junction-ambient ¹	75	°C/W	
R₀JC	Thermal Resistance Junction-Case ¹	4.32	°C/W	

P-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тр	Max.	Unit	
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	-30			V	
∆BVDSS/∆TJ	BVDSS Temperature Coefficient	Reference to 25°C , ID=-1mA		22		V/°C	
RDS(ON)	Static Drain-Source On-Resistance2	VGS=-10V , ID=-15A	32	38	42	mΩ	
		VGS=-4.5V , ID=-10A	48	60	70		
VGS(th)	Gate Threshold Voltage	VGS=VDS , ID =-250uA	-1.0		-2.5	V	
△VGS(th)	VGS(th) Temperature Coefficient			4.6		mV/°C	
		VDS=-24V, VGS=0V,			-1		
IDSS		TJ=25℃					
	-Drain-Source Leakage Current	VDS=-24V , VGS=0V ,			-5	⊢uA	
		TJ=55℃		İ			
IGSS	Gate-Source	VGS=±25V , VDS=0V			±100	nA	
	LeakageCurrent	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \					
gfs	Forward Transconductance	VDS=-5V , ID=-15A		19		S	
Rg	Gate Resistance	VDS=0V , VGS=0V , f=1MHz		13			
Qg	Total Gate Charge (-4.5V)			12.5			
Qgs	Gate-Source Charge	VDS=-15V , VGS=-4.5V , ID=-15A		5.4		nC	
Qgd	Gate-Drain Charge	-		5			
Td(on)	Turn-On Delay Time			4.4			
Tr	Rise Time	VDD=-15V , VGS=-10V , RG=3.3 ,		11.2		ns	
Td(off)	Turn-Off Delay Time	ID=-15A		34			
Tf	Fall Time			18			
Ciss	Input Capacitance			1345			
Coss	Output Capacitance	VDS=-15V , VGS=0V , f=1MHz		194		pF	
Crss	Reverse Transfer Capacitance			158		1	

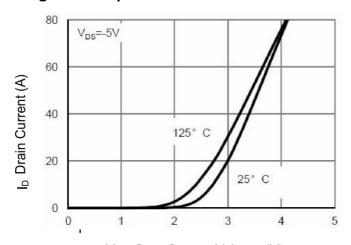
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

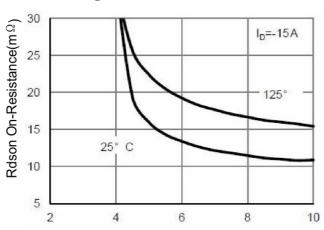


Typical Electrical and Thermal Characteristics

Figure 5 Output Characteristics



Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

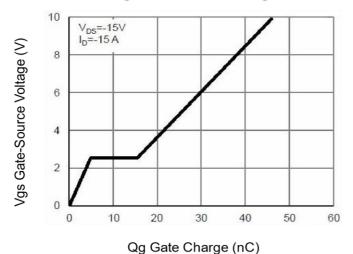


Figure 11 Gate Charge

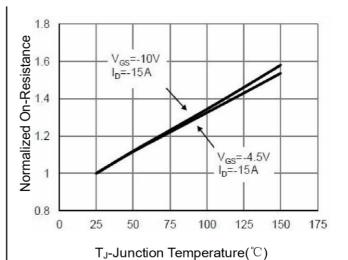
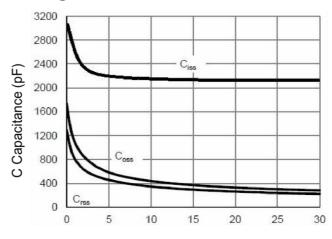
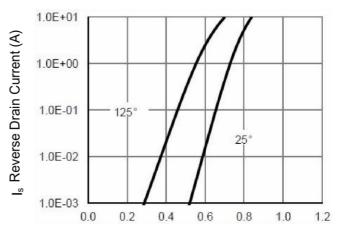


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward



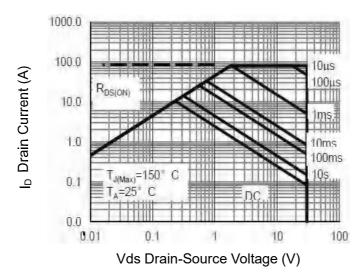


Figure 13 Safe Operation Area

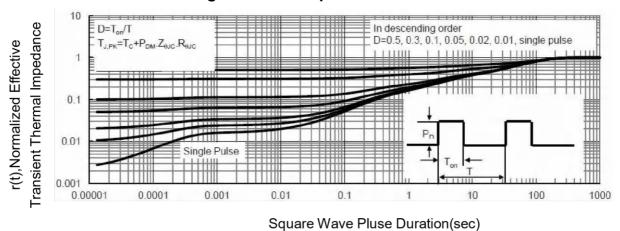
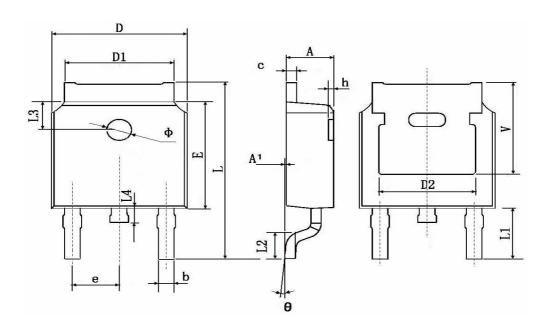


Figure 14 Normalized Maximum Transient Thermal Impedance

P-Channel Enhancement Mode MOSFET

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830 TYP.		0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3) TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	TYP.	0.211 TYP.			



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